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FDA28N50 N-Channel UniFETTM MOSFET 500 V, 28 A, 155 mΩ

Features

- $R_{DS(on)}$ = 122 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 14 A
- Low Gate Charge (Typ. 80 nC)
- Low C_{rss} (Typ. 42 pF)
- 100% Avalanche Tested
- RoHS Compliant

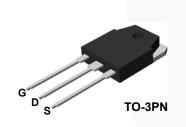
Applications

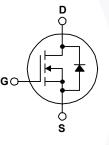
- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

May 2014

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

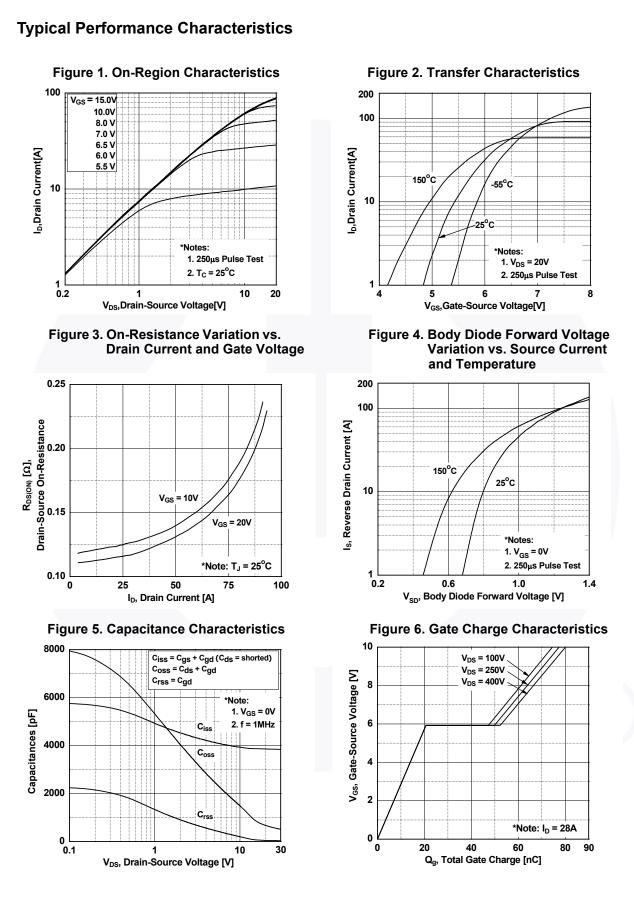
Symbol		FDA28N50	Unit			
V _{DSS}	Drain to Source Voltage			500	V	
V _{GSS}	Gate to Source Voltage			±30	V	
ID	Drain Current	- Continuous (T _C = 25 ^o C)	- Continuous (T _C = 25 ^o C)			
	Drain Current	- Continuous (T _C = 100 ^o C)		17	A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	112	А	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	2391	mJ	
I _{AR}	Avalanche Current		(Note 1)	28	А	
E _{AR}	Repetitive Avalanche Ener	(Note 1)	31	mJ		
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	5	V/ns	
P _D	Dower Dissinction	(T _C = 25 ^o C)		310	W	
	Power Dissipation	- Derate Above 25°C		2.5	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

Thermal Characteristics

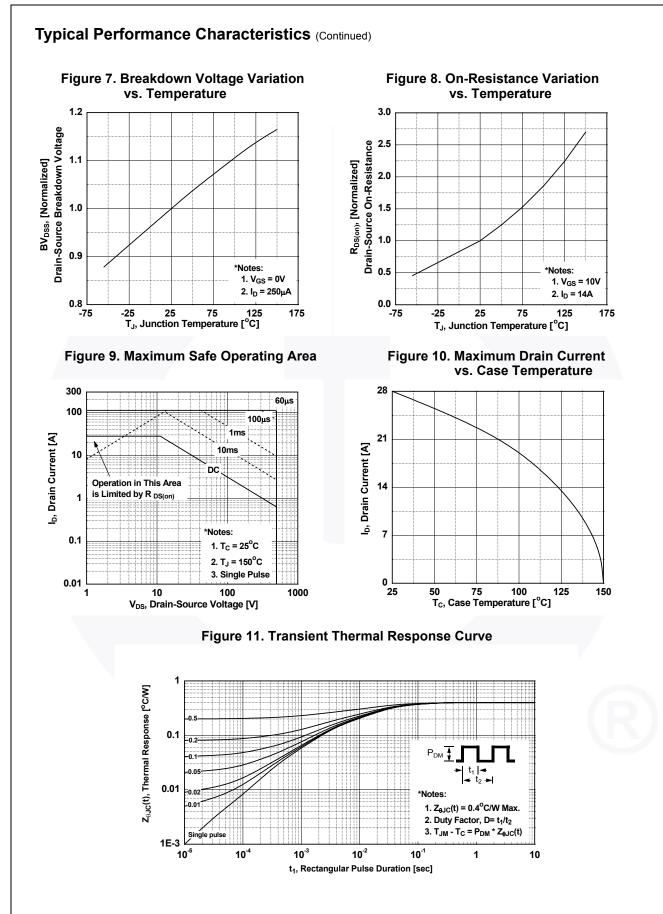
Symbol	Parameter	FDA28N50	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	o Case, Max. 0.4	
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/W

FDA28N50
— N-Channel
UniFET TM I
MOSFET

FDA28	mber	Part Number Top Mark F		Packing Method	Reel Size) Ta	ape Width	Qua	antity
	-		Package TO-3PN	Tube	N/A		N/A	30 units	
Electrica	l Chara	acteristics T _C = 25°C u	inless other	wise noted.					
Symbol	-			Test Conditions			Тур.	Max.	Unit
off Charac	teristics								
BV _{DSS}	1	Source Breakdown Voltage	lo =	I _D = 250 μA, V _{GS} = 0 V, T _J = 25 ^o C			-		V
∆BV _{DSS}		wn Voltage Temperature				500	0.50		V/°C
$/\Delta T_J$	Coefficie	ent		$I_D = 250 \ \mu$ A, Referenced to 25° C		-	0.59	-	V/°C
DSS	Zero Gat	Zero Gate Voltage Drain Current		= 500 V, V _{GS} = 0 V		-	-	1	μA
			-	$= 400 \text{ V}, \text{ T}_{\text{C}} = 125^{\circ}\text{C}$		-	-	10	
GSS	Gate to I	Body Leakage Current	V _{GS}	V_{GS} = ±30 V, V_{DS} = 0 V			-	±100	nA
On Charac	teristics	;							
V _{GS(th)}	Gate Th	reshold Voltage	V _{GS}	V _{GS} = V _{DS} , I _D = 250 μA		3.0	-	5.0	V
R _{DS(on)}	Static Dr	ain to Source On Resistance	e V _{GS}	$V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}$		-	0.122	0.155	Ω
9 _{FS}	Forward	Transconductance	V _{DS}	V _{DS} = 20 V, I _D = 14 A		-	34	-	S
Dynamic C	haracte	ristics							
C _{iss}	1	pacitance				-	3866	5140	pF
C _{oss}	- ·	Capacitance		_s = 25 V, V _{GS} = 0 V,	_		576	766	pr
S _{oss}	-	Transfer Capacitance	f = '	1 MHz		-	42	63	pF
$Q_{g(tot)}$	-	te Charge at 10V	.,	400.14		-	80	105	nC
Q _{gs}	-	Source Gate Charge		_S = 400 V, I _D = 28 A, _S = 10 V			21	-	nC
∝ _{gs} Q _{gd}	-	Drain "Miller" Charge	v GS	5 - 10 V	(Note 4)	-	32	-	nC
		ů							
Switching									
d(on)		Delay Time	V	- 250 \/ - 29 A		-	56	122	ns
r		Rise Time		V_{DD} = 250 V, I _D = 28 A, V_{GS} = 10 V, R _G = 25 Ω		-	126	262	ns
d(off)		Delay Time	. 65			•	210	430	ns
f	Turn-Off	Fall Time			(Note 4)	-	110	230	ns
Drain-Sour	ce Diod	e Characteristics							
s	Maximun	n Continuous Drain to Source	e Diode For	ward Current		7-	-	28	Α
I _{SM}	Maximun	n Pulsed Drain to Source Dic	de Forward	Current		-	-	112	Α
V _{SD}	Drain to \$	Source Diode Forward Voltag	ge V _{GS}	_s = 0 V, I _{SD} = 28 A		-	-	1.4	V
rr	Reverse	Recovery Time		_s = 0 V, I _{SD} = 28 A,		-	530		ns
2 ^{rr}	Reverse	Recovery Charge	dl _F /	dt = 100 A/µs		-	8		μC



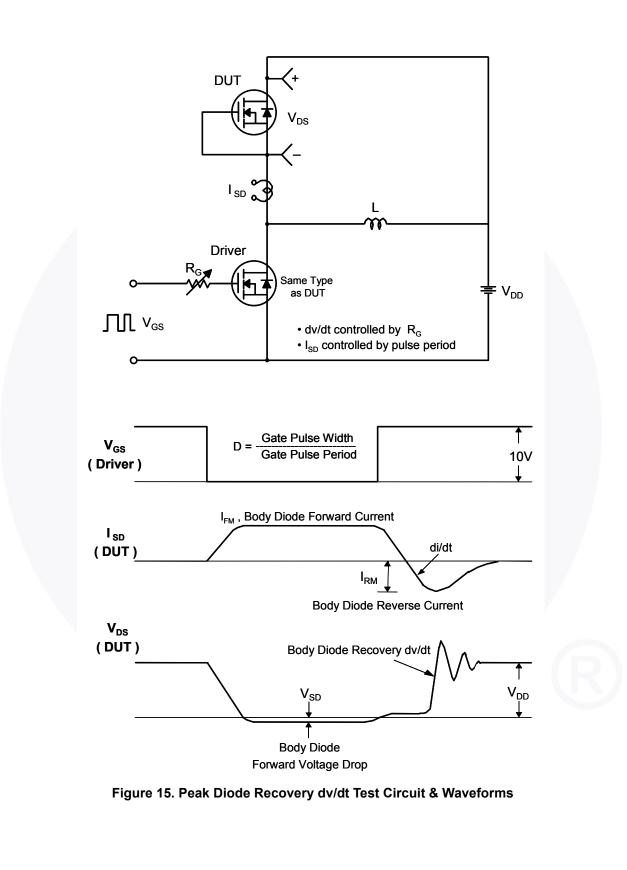
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 V_{GS} Ş R Q_g F V_{DS} Q_{gs} Q_{gd} • DUT I_G = const. Charge Figure 12. Gate Charge Test Circuit & Waveform R VDS V_{DS} 90% ο V_{DD} GS R_{G} 10% V_{GS} DUT V_{GS} ∏ o Figure 13. Resistive Switching Test Circuit & Waveforms L $E_{AS} = \frac{1}{2} L I_{AS}^2$ V_{DS} $\mathsf{BV}_{\mathsf{DSS}}$ ID o IAS R_{G} ≑ V_{DD} $I_D(t)$ V_{GS} V_{DD} $V_{DS}(t)$ DUT Time t_p Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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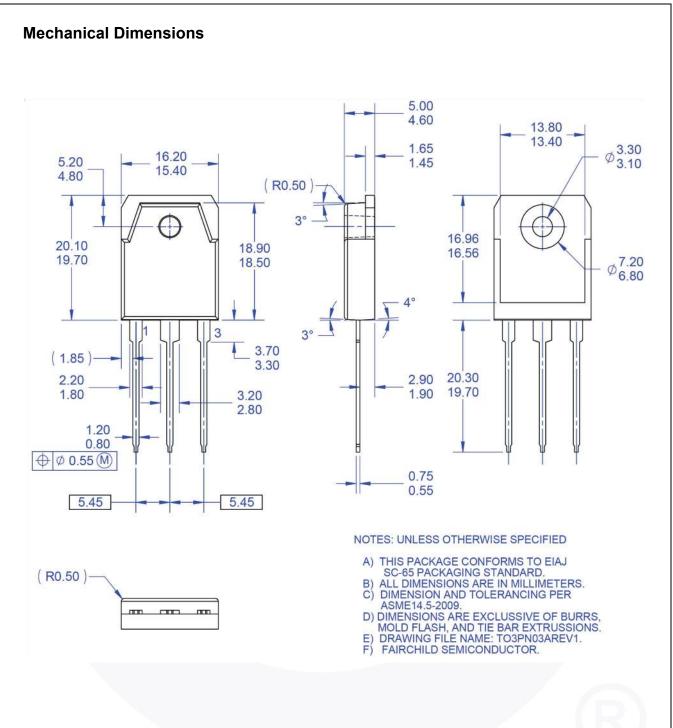


Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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FDA28N50 — N-Channel UniFETTM MOSFET



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